

HiPerFET™ Power MOSFET

IXFN180N20

N-Channel Enhancement Mode Avalanche Rated Fast Intrinsic Rectifier



Symbol	Test Conditions	Maximum Ratings		
V _{DSS}	T _J = 25°C to 150°C	200	V	
V _{DGR}	$T_J = 25$ °C to 150°C, $R_{GS} = 1M\Omega$	200	V	
V _{GSS}	Continuous	±20	V	
V _{GSM}	Transient	±30	V	
I _{D25}	T _C = 25°C	180	A	
I _{DM}	$T_{\rm C} = 25^{\circ}$ C, Pulse Width Limited by $T_{\rm JM}$	720	А	
I _A E _{AS}	T _c = 25°C T _c = 25°C	36 4	A J	
dv/dt	$I_{S} \leq I_{DM}, V_{DD} \leq V_{DSS}, T_{J} \leq 150$ °C	5	V/ns	
$\overline{\mathbf{P}_{\mathrm{D}}}$	T _C = 25°C	700	W	
T _J T _{JM} T _{stg}		-55 +150 150 -55 +150	0° 0° 0°	
V _{ISOL}	50/60 Hz, RMS, t = 1minute	2500	V~	
	$I_{ISOL} \le 1 \text{mA}, \qquad t = 1 \text{s}$	3000	٧~	
M _d	Mounting Torque for Base Plate Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in Nm/lb.in	
Weight		30	g	

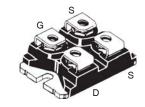
	I _{D25} R _{DS(on)}
P D	t _{rr}



≤

<

V_{DSS}



200V

180A

12.5m Ω 250ns

G = Gate S = Source D = Drain

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Features

- International Standard Package
- miniBLOC with Aluminum Nitride Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- ${}^{\bullet}$ Low ${\rm R_{\rm DS(on)}}$ and ${\rm Q_{\rm G}}$

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- AC Choppers
- Temperature and Lighting Controls

Symbol (T _J = 25°C U	Test Conditions Inless Otherwise Specified)	Chara Min.	cteristic Typ.	Values Max	
BV _{DSS}	$V_{GS} = 0V, I_D = 3mA$	200			V
V _{GS(th)}	$V_{DS} = V_{GS}$, $I_{D} = 8mA$	2.0		4.0	V
I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			±200	nA
I _{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_{J} = 1$	25°C		100 2	μA mA
R _{DS(on)}	$V_{GS} = 10V, I_{D} = 90A, Note 1$			12.5	mΩ



Symbol	Test Conditions	Characteristic Values		
$(T_J = 25^{\circ}C)$	C Unless Otherwise Specified)	Min.	Тур.	Max.
g _{fs}	$V_{DS} = 15V, I_{D} = 60A, Note 1$	90	130	S
C _{iss})		22	nF
C _{oss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		3800	pF
C _{rss}	J		600	pF
t _{d(on)}	Resistive Switching Times		55	ns
t _r			85	ns
$\mathbf{t}_{d(off)}$	$\begin{cases} V_{GS} = 10V, V_{DS} = 0.5 \bullet V_{DSS}, I_{D} = 90A \\ R_{G} = 1\Omega \text{ (External)} \end{cases}$		180	ns
t _f			56	ns
Q _{g(on)})		660	nC
\mathbf{Q}_{gs}	$ V_{GS} = 10V, V_{DS} = 0.5 \bullet V_{DSS}, I_{D} = 90A $		120	nC
\mathbf{Q}_{gd}			270	nC
R _{thJC}				0.18 °C/W
R _{thCS}			0.05	°C/W

SOT-227B (IXFN) Outline (M4 screws (4x) supplied) SYM INCHES MILLIMETERS MIN MAX MIN MAX A 1.240 1.255 31.50 31.88 B .307 .323 7.80 8.20 C .161 1.69 4.09 4.29 D .161 1.69 4.09 4.29 E .161 1.69 4.09 4.29 E .161 1.69 4.09 4.29 F .587 .595 14.91 15.11 G .1186 1.193 30.12 30.30 H .1496 1.505 38.00 38.23 J .460 481 11.68 12.22 K .351 .378 8.92 9.60 L .030 0.33 0.76 0.84 M .496 .506 12.60 12.85 N .990 1.001 25.15 25.42 O .078 .084 1.98 2.13 P .195 2.35 4.95 5.97 Q .1045 1.059 26.54 26.90 R .155 .174 3.94 4.42 S .186 .191 4.72 4.85 T .968 .987 24.59 25.07 U .002 .004 -0.05 0.1

Source-Drain Diode

Symbol Test Conditions (T _J = 25°C Unless Otherwise Specified)		Chara Min.	/alues Max.	
I _s	$V_{GS} = 0V$			180 A
I _{sm}	Repetitive, Pulse Width Limited by $T_{_{\rm JM}}$			720 A
V _{SD}	$I_{\rm F} = 100 {\rm A}, V_{\rm GS} = 0 {\rm V}, {\rm Note} 1$			1.2 V
$\left\{ egin{array}{c} \mathbf{t}_{rr} \\ \mathbf{Q}_{RM} \\ \mathbf{I}_{RM} \end{array} \right\}$	$I_F = 50A$, -di/dt = 100A/ μ s $V_R = 100V$, $V_{GS} = 0V$		1.5 10	250 ns μC A

Note 1. Pulse test, $t \le 300\mu s$, duty cycle, $d \le 2\%$.

